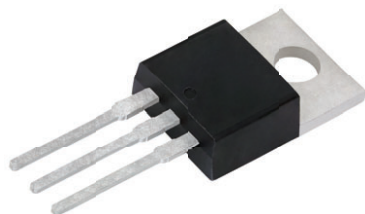
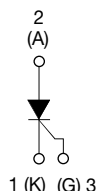


Thyristor High Voltage, Phase Control SCR, 16 A



3L TO-220AB



FEATURES

- Designed and qualified according to JEDEC®-JESD 47
- 125 °C max. operating junction temperature
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge

DESCRIPTION

The VS-16TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operating up to 125 °C junction temperature.

PRIMARY CHARACTERISTICS

$I_{T(AV)}$	10 A
V_{DRM}/V_{RRM}	800 V, 1200 V
V_{TM}	1.4 V
I_{GT}	60 mA
T_J	-40 °C to 125 °C
Package	3L TO-220AB
Circuit configuration	Single SCR

OUTPUT CURRENT IN TYPICAL APPLICATIONS

APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
Capacitive input filter $T_A = 55\text{ °C}$, $T_J = 125\text{ °C}$, common heatsink of 1 °C/W	13.5	17	A

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	10	A
I_{RMS}		16	
V_{DRM}/V_{RRM}	Range ⁽¹⁾	800, 1200	V
I_{TSM}		200	A
V_T	10 A, $T_J = 25\text{ °C}$	1.4	V
dV/dt		500	V/μs
dI/dt		150	A/μs
T_J	Range	-40 to +125	°C

Note

⁽¹⁾ For higher voltage up to 1600 V contact factory

VOLTAGE RATINGS

PART NUMBER	V_{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM}/I_{DRM} AT 125 °C mA
VS-16TTS08-M3	800	800	10
VS-16TTS12-M3	1200	1200	

**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			TYP.	MAX.	
Maximum average on-state current	$I_{T(AV)}$	$T_C = 98\text{ }^{\circ}\text{C}$, 180° conduction, half sine wave	10		A
Maximum RMS on-state current	I_{RMS}		16		
Maximum peak, one-cycle, non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied	170		
		10 ms sine pulse, no voltage reapplied	200		
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied	144		A^2s
		10 ms sine pulse, no voltage reapplied	200		
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1$ to 10 ms, no voltage reapplied	2000		$A^2\sqrt{s}$
Maximum on-state voltage drop	V_{TM}	10 A, $T_J = 25\text{ }^{\circ}\text{C}$	1.4		V
On-state slope resistance	r_t	$T_J = 125\text{ }^{\circ}\text{C}$	24.0		$m\Omega$
Threshold voltage	$V_{T(TO)}$		1.1		V
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	$T_J = 25\text{ }^{\circ}\text{C}$	$V_R = \text{Rated } V_{RRM}/V_{DRM}$		mA
		$T_J = 125\text{ }^{\circ}\text{C}$			
Holding current	I_H	Anode supply = 6 V, resistive load, initial $I_T = 1$ A 16TTS08PbF, 16TTS12PbF, $T_J = 25\text{ }^{\circ}\text{C}$	-	150	
Maximum latching current	I_L	Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	200		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max.}$, linear to $80\text{ }^{\circ}\text{C}$, $V_{DRM} = R_g - k = \text{Open}$	500		V/ μs
Maximum rate of rise of turned-on current	dI/dt		150		A/ μs

TRIGGERING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	
Maximum peak positive gate current	$+I_{GM}$		1.5	A
Maximum peak negative gate voltage	$-V_{GM}$		10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^{\circ}\text{C}$	90	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	60	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^{\circ}\text{C}$	35	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, $T_J = -65\text{ }^{\circ}\text{C}$	3.0	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^{\circ}\text{C}$	2.0	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^{\circ}\text{C}$	1.0	
Maximum DC gate voltage not to trigger	V_{GD}	$T_J = 125\text{ }^{\circ}\text{C}$, $V_{DRM} = \text{Rated value}$	0.25	mA
Maximum DC gate current not to trigger	I_{GD}		2.0	

SWITCHING

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t_{gt}	$T_J = 25\text{ }^{\circ}\text{C}$	0.9	μs
Typical reverse recovery time	t_{rr}	$T_J = 125\text{ }^{\circ}\text{C}$	4	
Typical turn-off time	t_q		110	



THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.3	°C/W
Maximum thermal resistance, junction to ambient	R _{thJA}		62	
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight			2	g
			0.07	oz.
Mounting torque	minimum		6 (5)	kgf · cm (lbf · in)
	maximum		12 (10)	
Marking device		Case style 3L TO-220AB	16TTS08	
			16TTS12	

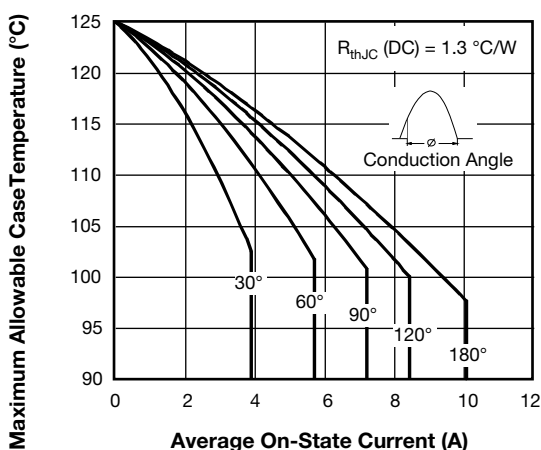


Fig. 1 - Current Rating Characteristics

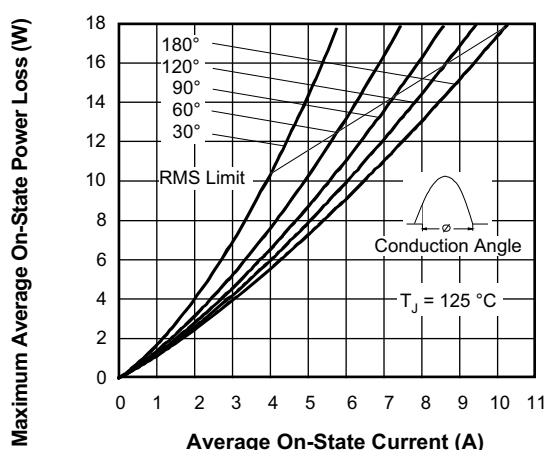


Fig. 3 - On-State Power Loss Characteristics

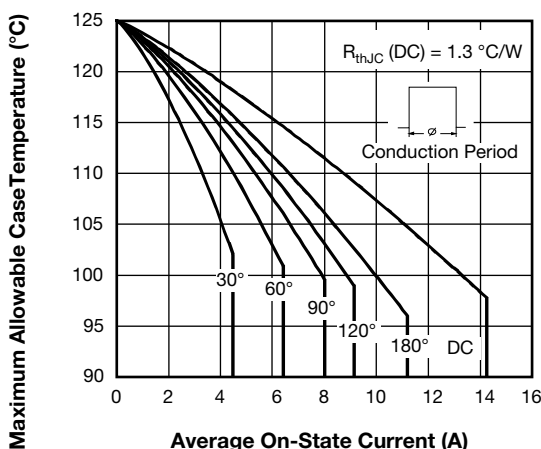


Fig. 2 - Current Rating Characteristics

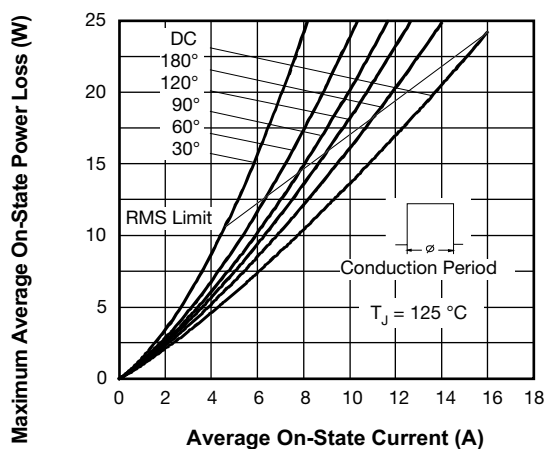


Fig. 4 - On-State Power Loss Characteristics

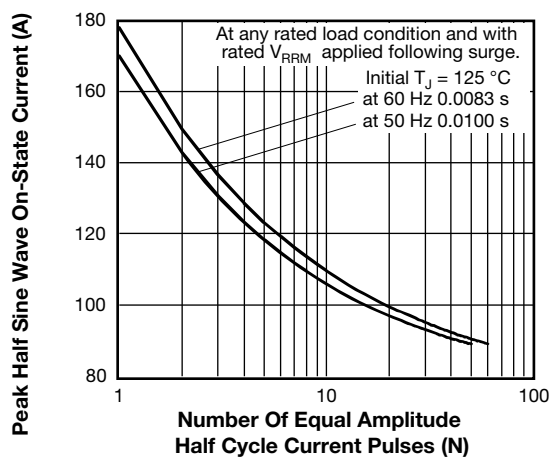


Fig. 5 - Maximum Non-Repetitive Surge Current

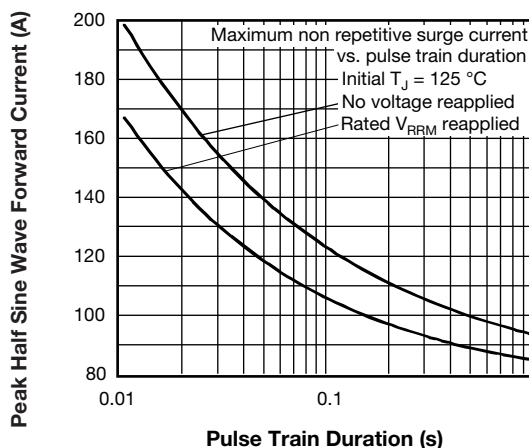


Fig. 6 - Maximum Non-Repetitive Surge Current

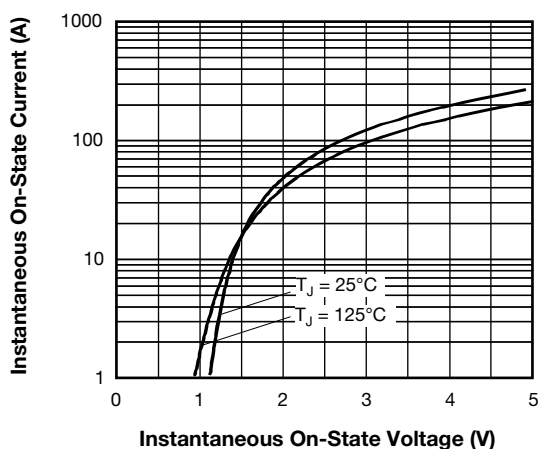
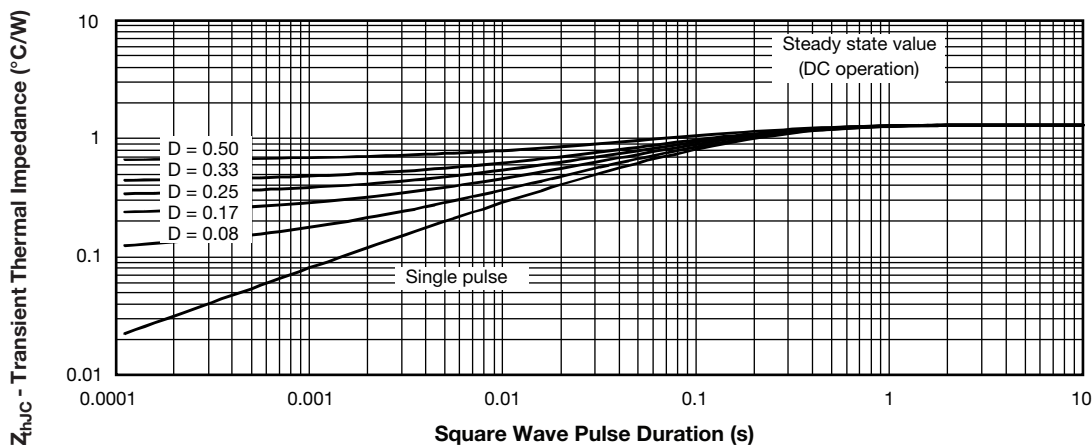


Fig. 7 - On-State Voltage Drop Characteristics


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

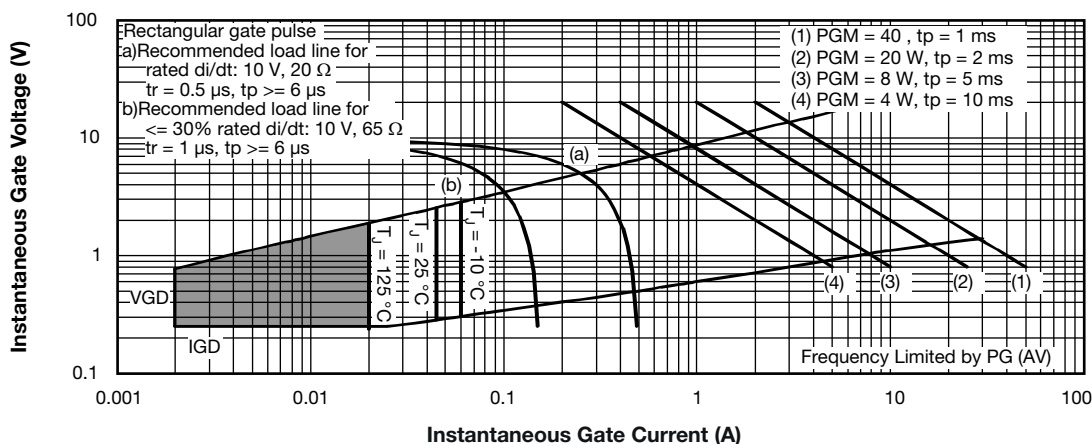


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	16	T	T	S	12	-M3
	1	2	3	4	5	6	7

- 1 - Vishay Semiconductors product
- 2 - Current rating
- 3 - Circuit configuration:
T = single thyristor
- 4 - Package:
T = TO-220AB
- 5 - Type of silicon:
S = converter grade
- 6 - Voltage code x 100 = V_{RRM} — 08 = 800 V
12 = 1200 V
- 7 - Environmental digit:
-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

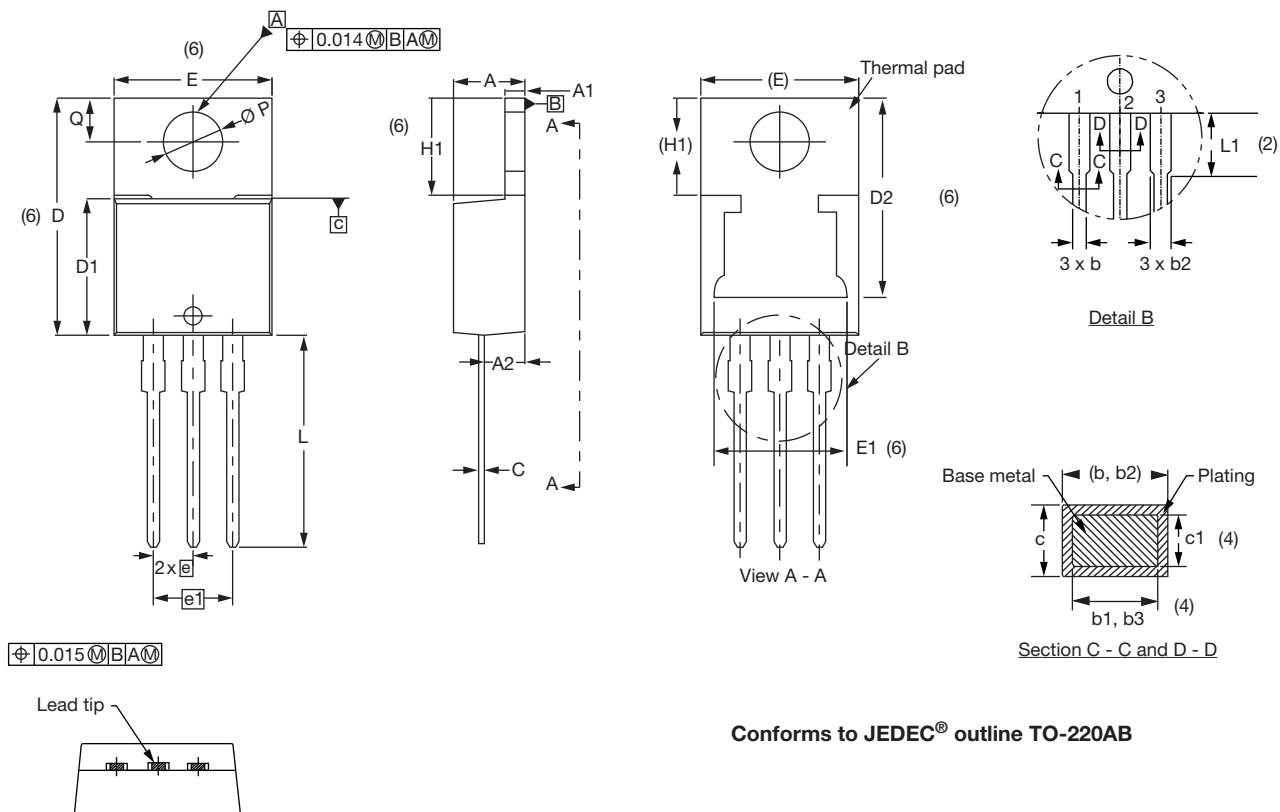
ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-16TTS08-M3	50	1000	Antistatic plastic tubes
VS-16TTS12-M3	50	1000	Antistatic plastic tubes

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96154
Part marking information	www.vishay.com/doc?95028



3L TO-220AB

DIMENSIONS in millimeters and inches



Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
c	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	13.30	0.460	0.524	6, 7
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
e	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØP	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Notes

- Dimensioning and tolerancing as per ASME Y14.5M-1994
- Lead dimension and finish uncontrolled in L1
- Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- Thermal pad contour optional within dimensions E, H1, D2, and E1
- Outline conforms to JEDEC® TO-220, except D2



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